

What is claimed is:

1. A nitride semiconductor device comprising:
at least a p-type nitride semiconductor layer;
5 an electrode including at least rhodium and iridium; and
wherein said electrode is formed on said p-type nitride
semiconductor layer.

2. The nitride semiconductor device according to
10 claim 1, wherein said electrode having an at least
two-layer structure wherein iridium is laminated on
rhodium which is laminated in contact with said p-type
nitride semiconductor layer.

15 3. The nitride semiconductor device according to
claim 2, wherein the film thickness of rhodium in said
two-layer structure being from equal or greater than 10
Å to equal or less than 1000 Å.

20 4. The nitride semiconductor device according to
claim 1, wherein said electrode being annealed at equal
or greater than 300 °C.